

Table of Contents

Preface

iv

I. Keynote Address

Design: New Material Challenge for Silicon ULSI

L.C. Kimerling

1

II. Silicon Materials

Silicon Wafer Technology: The Challenges towards the Gigabit Era

A.P. Mozer

9

Hydrogen Annealed Silicon Wafer

S. Nadahara, H. Kubota and S. Samata

19

Formation of Microscopic Distribution of Grown-In Defects in Czochralski Silicon Crystal

R. Habu, K. Kawakami and M. Hasebe

27

CZ Crystal Growth Development in Super Silicon Crystal Project

H. Yamagishi, M. Kuramoto, Y. Shiraishi, M. Machida, K. Takano, N. Takase, T. Iida, J. Matsubara and K. Takada

37

III. Gettering Techniques

Gettering by Voids in Silicon: A Comparison with other Techniques

V. Raineri

43

Gettering in Advanced Low Temperature Processes

S. Sadamitsu, S. Ogushi, Y. Koike, N. Reilly, T. Nagashima, M. Sano and H. Tsuya

53

Metal Gettering by Defective Regions in Carbon-Implanted Silicon

R. Kögler, J.R. Kaschny, R.A. Yankov, P. Werner, A.B. Danilin and W. Skorupa

63

Metallic Impurity Gettering in MeV Implanted Si

O.V. Kononchuk, R.A. Brown, S.V. Koveshnikov, K.L. Beaman, F. Gonzalez and G.A. Rozgonyi

69

Influence of Size and Density of Oxygen Precipitates of Internal Gettering Efficiency of Iron in Czochralski-Grown Silicon

H. Takahashi, H. Yamada-Kaneta and M. Suezawa

75

A Quantitative Method of Metal Impurities Depth Profiling for Gettering Evaluation in Silicon Wafers

M.B. Shabani, T. Yoshimi, S. Okuuchi and A. Kaniava

81

Oxygen Gettering on Buried Layers at Post-Implantation Annealing of Hydrogen Implanted Czochralski Silicon

R. Job, W.R. Fahrner, A.G. Ulyashin, Y.A. Bumay, A.I. Ivanov and L. Palmetshofer

91

Use of Gettering and Defect Induced Processes in Ultra-Thin Buried Oxide Synthesis

V.G. Litovchenko, A.A. Efremov, B.N. Romanyuk, V.P. Melnik and C. Claeys

97

Interaction of Impurities and Dislocations in Silicon before and after External Gettering

I. Périchaud and S. Martinuzzi

103

The Influence of Intrinsic Point Defects on Getter Formation in Silicon Wafers

M.G. Mil'vidskii, V.V. Voronkov, K.L. Enisherlova and V.J. Reznick

109

Comparison of External Gettering Efficiency of Phosphorus Diffusion, Aluminium-Silicon Alloying and Helium Implantation in Silicon Wafers

N. Gay and S. Martinuzzi

115

IV. Oxygen in Silicon

Effect of High Temperature Pre-Anneal on Oxygen Precipitates Nucleation Kinetics in Si

R.J. Falster, M. Cornara, D. Gambaro, M. Olmo and M. Pagani

123

Vacancy-Assisted Oxygen Precipitation Phenomena in Si	129
R.J. Falster, M. Pagani, D. Gambaro, M. Cornara, M. Olmo, G. Ferrero, P. Pichler and M. Jacob	
Mechanism of Slip Dislocation Generation by Oxide Precipitates in Czochralski Silicon Wafers	137
K. Sueoka, M. Akatsuka, H. Katahama and N. Adachi	
State of Oxygen and Growth Conditions	143
T.M. Tkacheva and G.N. Petrov	
Analyzing Oxygen Precipitation Using the Surface Photovoltage Technique (SPV)	149
P. Moens, W. Dobbelaere and T. Colpaert	
Study of Oxygen Related Recombination Defects in Si by Temperature-Dependent Lifetime and EBIC Measurements	155
E. Gaubas, J. Vanhellemont, E. Simoen, C. Claeys and W. Seifert	
Oxygen Precipitate Nucleation Process in Silicon with Different Oxygen Concentration and Structural Perfection	161
I.V. Antonova, A. Misiuk, V.P. Popov, A.E. Plotnikov and B. Surma	
Initial Stage of Oxygen Precipitation in Silicon	167
A. Kornylo, A. Maksymov, M. Pashkovski and I. Savytskii	
Oxygen Precipitation in Silicon Thin Layers in the Presence of Carbon	171
T.M. Tkacheva, G.N. Petrov, K.L. Enisherlova and T.F. Rusak	
Heterogeneous Precipitation of Silicon Oxide in Silicon at Laser Induced Centres	177
Y. Blums and A. Medvid	
Diffusion and Precipitation of Oxygen in Silicon Doped with Germanium	183
L.I. Khirunenko, Y.V. Pomozov, V.I. Shakhovtsov and V.V. Shumov	
Low-Temperature Doping of P-Type Czochralski Silicon due to Hydrogen Plasma Enhanced Thermal Donor Formation	189
A.G. Ulyashin, Y.A. Bumay, R. Job, G. Grabosch, D. Borchert, W.R. Fahrner and A.Y. Diduk	

V. Erbium in Silicon

Erbium in Silicon: Problems and Challenges	197
S. Binetti, M. Donghi, S. Pizzini, A. Castaldini, A. Cavallini, B. Fraboni and N.A. Sobolev	
Thermal Donors in Silicon Doped with Erbium	207
V.V. Emtsev, N.A. Sobolev, B.A. Andreev, D.S. Poloskin and E.I. Shek	
Radiation Induced Defects InGaAs Photodiodes by 1-MeV Fast Neutrons	213
H. Ohyama, E. Simoen, C. Claeys, J. Vanhellemont, T. Kudou, Y. Takami and H. Sunaga	

VI. Radiation Effects in Semiconductors

Defect Engineering Radiation Tolerant Silicon Detectors	221
B.C. MacEvoy and S.J. Watts	
Microscopic Studies of Radiation Damage-Induced Defects Responsible for the Deterioration of High-Resistivity Silicon Detectors	233
H. Feick and M. Moll	
Lattice Defects in $\text{Si}_{1-x}\text{Ge}_x$ Devices by Proton Irradiation and their Effect on Device Performance	239
H. Ohyama, E. Simoen, C. Claeys, J. Vanhellemont, Y. Takami, H. Sunaga, J. Poortmans and M. Caymax	
An IR Study of the Annealing Behaviour of A-Center in Silicon	245
C.A. Londos, N.V. Sarlis and L.G. Fytros	
Lifetime Considerations for High-Energy Proton Irradiated Si p-n Junction Diodes	251
E. Simoen, J. Vanhellemont and C. Claeys	
Defect Formation during Erbium Implantation and Subsequent Annealing of Si:Er	257
N.A. Sobolev, A.M. Emel'yanov, Y.A. Kudryavtsev, R.N. Kyutt, M.I. Makovijchuk, Y.A. Nikolaev, E.O. Parshin, V.I. Sakharov, I.T. Serenkov, E.I. Shek and K.F. Shtel'makh	
Alpha-Particle Irradiation Induced Defects in Metal-Oxide-Semiconductor Silicon Transistor	263
B.P. Koman, R.R. Ivanochko and A.K. Shkolnyy	

The Change of Au-ZnS and Au-CdS Diode Structure Parameters Caused by Low-Dose X-Ray Irradiation

B. Pavlyk, Y. Horyn' and B. Tsybulyak

269

VII. Dislocations in Silicon

Critical Resolved Shear Stress for a Dislocation Loop Growth, Stability and Retrogrowth in Silicon: Application to the 16 MEG DRAM

B. Leroy

275

Modification of the Recombination Activity of Dislocations in Silicon by Hydrogenation, Phosphorous Diffusion and Heat Treatments

W. Seifert, K. Knobloch and M. Kittler

287

Influence of Electric Field-Enhanced Emission on Deep Level Transient Spectra of Bandlike Extended Defects: NiSi₂-Precipitates in Silicon

H. Hedemann and W. Schröter

293

The Effect of Dislocation Dissociation on the g-Tensor of Holes in Dislocation Related 1D Energy Band in Si

V.V. Kveder, A.I. Shalynin, E.A. Steinman and A.N. Izotov

299

Influence of the Surface Metal Spraying on the Dislocation Detachment Process in Silicon Crystals

V.A. Makara, L.P. Steblenko and A.M. Kolomiyets

305

The Magnesium Related Luminescence in Silicon and its Quenching due to the Presence of Dislocations

E.A. Steinman, H.S. Leipner and H.G. Grimmeiss

313

Deformation Interaction of Defects in Crystal: Concept of Evaluation

M.D. Efremov

319

VIII. Defect Engineering

Yield Analysis of CMOS ICs

D. Schmitt-Landsiedel

327

The Role of Grown-in Defects in Advanced Silicon Technology

G. Kissinger, D. Gräf, J. Vanhellemont, U. Lambert and H. Richter

337

Point Defect and Microdefect Dynamics in Czochralski-Grown Silicon: Simulations and Analysis of Self-Consistent Models

T. Sinno and R.A. Brown

343

Observation of Vacancy Enhancement during Rapid Thermal Annealing in Nitrogen

M. Jacob, P. Pichler, H. Ryssel, R.J. Falster, M. Cornara, D. Gambaro, M. Olmo and M. Pagani

349

Strain and Gettering in Epitaxial Silicon Wafers

F.G. Kirsch, M.B. Shabani, T. Yoshimi, S.B. Kim, B. Snegirev, C.M. Wang, L. Williamson, K. Takashima, P. Taylor and D. Lange

355

Strain in Silicon below Si₃N₄ Stripes, Comparison between SUPREM IV Calculation and TEM/CBED Measurements

A. Armigliato, R. Balboni, S. Frabboni, A. Tixier, G.P. Carnevale, P. Colpani and A. Marmiroli

365

Defects Produced in Silicon by Reactive Ion Etching

H.B. Erzgräber, H.H. Richter, M.-. Aminpur, A. Wolff and K. Blum

371

Depth Dependence of Dislocation Loop Dissolution Kinetics in Ion Implanted Silicon

M. Seibt, Y.L. Huang and B. Plikat

377

Hydrogen Stimulated Destruction of Fe-B Pairs in p-Si

E.B. Yakimov and A.L. Parakhonsky

383

Differential Interference Contrast Microscopy of Defects in As-Grown and Annealed Si Wafers

M.-. Trauwaert, J. Vanhellemont, U. Lambert, D. Gräf, K. Kenis, P.W. Mertens and M. Heyns

387

Effect of Stress Induced Defects on Electrical Properties of Czochralski Grown Silicon

A. Misiuk, W. Jung, B. Surma, J. Jun and M. Rozental

393

IX. Advanced Semiconductor Materials and Devices

Planar Solidification of Multicrystalline Silicon for Phtovoltaic Applications	
W. Koch, C. Häbler, H.-. Höfs, A. Müller and I.A. Schwirtlich	401
Implementation of Low Thermal Budget Techniques to Si and SiGe MOSFET Device Processing	
M. Glück, J. Hersener, H.G. Umbach, J. Rappich and J. Stein	413
Ge Concentration Effect on the Dislocation Mobility in the Bulk SiGe Alloy Single Crystals	
Y.L. Iunin, V.I. Orlov, D.V. Dyachenko-Dekov, N.V. Abrosimov, S.N. Rossolenko and W. Schröder	419
On the Defect Structures in Te-Doped GaAs	
C. Frigeri, J.L. Weyher, J. Jiménez, P. Martín and S. Müller	425
Study of Surface Conduction Related Effects in GaAs MESFET's	
V.R. Balakrishnan, V. Kumar and S. Ghosh	431
Nitridation Effects in n-CdTe	
S. Gurumurthy, H.L. Bhat and V. Kumar	441

X. Semiconductor Material and Device Diagnostics

Formation of Grown-in Defects in CZ-Si Crystals	
M. Hasebe, K. Nakai, W. Ohashi, Y. Ikematsu, T. Mizutani and T. Iwasaki	449
X-Ray Diffractometry and Admittance Spectroscopy Investigation of Silicon Implanted at Low Energies with Oxygen, Argon, or Silicon	
P. Zaumseil and S. Kar	459
Peculiarities of Raman Spectra and Real Structure of $\text{Ge}_{1-x}\text{Si}_x$ Solid Solution	
B. Dietrich and L.K. Orlov	465
Computer Simulation of Impurity Diffusion in the Vicinity of Grain Boundaries (Modified Fisher Model)	
A.K. Fedotov, M. Chuiko, A. Rabysko and S. Shumski	471
Improved Extraction of Si Substrate Parameters from Combined I-V and C-V Measurements on P-N Junction Diodes	
A. Czerwinski, E. Simoen, J. Vanhellemont, D. Tomaszewski, J. Gibki and A. Bakowski	477
An Experimental Study of Ion Beam and ECR Hydrogenation of Self-Ion Implantation Damage in Silicon by Admittance Spectroscopy and X-Ray Triple Crystal Diffractometry	
S. Kar, P. Zaumseil and S. Ashok	483
Positron Annihilation Rate and Broad Component of 1D-ACAR in Cz-Si and Fz-Si	
N.Y. Arutyunov	489
Capacitance Spectroscopy of Thin GaAs Layers Grown by Molecular Beam Epitaxy at Low Temperatures	
V.V. Chaldyshev, P.N. Brounkov, A.A. Suvorova, S.G. Konnikov, V.V. Preobrazhenski, M.A. Putyato and B.R. Semyagin	495
Raman Spectroscopy Investigation of Silicon Nanocrystals Formation in Silicon Nitride Films	
V.A. Volodin, M.D. Efremov and V.A. Gritsenko	501
Raman and HREM Observation of Oriented Silicon Nanocrystals Inside Amorphous Silicon Films on Glass Substrates	
M.D. Efremov, V.V. Bolotov, V.A. Volodin, L.I. Fedina, A.A. Gutakovskij and S.A. Kochubei	507
A Model of Coupled Diffusion of Impurity Atoms and Point Defects in the Vicinity of Semiconductor Interfaces and Grain Boundaries	
O. Velichko and A.K. Fedotov	513
New Possibility of Impurities Express Determination by Laser Element Spark-Analyzer (LESA)	
T.M. Tkacheva, G.N. Petrov and D.V. Vlasov	519
Analytical Modeling of the Gold Diffusion Induced Modification of the Forward Current through P-N Silicon Junctions	
F. Gaiseanu, M. Sachelarie, D. Sachelarie and J. Esteve	525